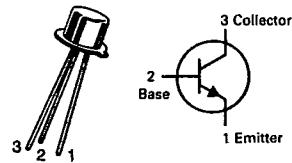


T-27-09

**2N915****CASE 22-03, STYLE 1  
TO-18 (TO-206AA)****GENERAL PURPOSE  
TRANSISTOR  
NPN SILICON**

Refer to 2N3946 for graphs.

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**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector-Base Voltage	$V_{CBO}$	70	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0	Vdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	0.36 2.05	Watts mW/C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.2 6.81	Watts mW/C
Total Power Dissipation @ $+ 100^\circ\text{C}$ Case	$P_D$	0.68	W
Operating and Storage Temperature Temperature Range	$T_J, T_{Stg}$	-65 to +200	°C

**ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)**

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Sustaining Voltage(1) ( $I_C = 10 \text{ mA } I_B = 0$ )	$V_{CEO(sus)}$	50	—	Vdc
Collector-Base Breakdown Voltage ( $I_C = 100 \mu\text{A } I_E = 0$ )	$V_{(BR)CBO}$	70	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10 \mu\text{A}, I_C = 0$ )	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ( $V_{CB} = 60 \text{ V}, I_E = 0$ )	$I_{CBO}$	—	0.010	$\mu\text{A}$
Collector Cutoff Current ( $V_{CB} = 60 \text{ V}, I_E = 0$ ) ( $V_{CB} = 60 \text{ V}, I_E = 0, T_A = +150^\circ\text{C}$ )	$I_{CBO}$	—	0.010 30	$\mu\text{A}$
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 10 \text{ mA } V_{CE} = 5.0 \text{ V}$ )	$h_{FE}$	50	200	—
Collector-Emitter Saturation Voltage ( $I_C = 10 \text{ mA } I_B = 1.0 \text{ mA}$ )	$V_{CE(\text{sat})}$	—	1.0	Vdc
Base-Emitter Saturation Voltage ( $I_C = 10 \text{ mA } I_B = 1.0 \text{ mA}$ )	$V_{BE(\text{sat})}$	—	0.9	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Output Capacitance ( $I_E = 0 \text{ V}_{CB} = 10 \text{ V}, f = 100 \text{ kHz}$ )	$C_{obo}$	—	3.5	pF
Emitter Transition Capacitance ( $I_C = 0 \text{ V}_{EB} = 0.5 \text{ V}, f = 100 \text{ kHz}$ )	$C_{TE}$	—	10	pF
Input Impedance ( $I_C = 1.0 \text{ mA } V_{CE} = 5.0 \text{ V}$ ) ( $I_C = 5.0 \text{ mA } V_{CE} = 5.0 \text{ V}$ )	$h_{ie}$	—	6000 2000	ohms
High Frequency Current Gain $f = 100 \text{ MHz}$ ( $I_C = 10 \text{ mA } V_{CE} = 15 \text{ V}$ )	$h_{fe}$	2.5	—	—
Small-Signal Current Gain $f = 1 \text{ kHz}$ ( $I_C = 1.0 \text{ mA } V_{CE} = 5.0 \text{ V}$ ) ( $I_C = 5.0 \text{ mA } V_{CE} = 5.0 \text{ V}$ )	$h_{fe}$	40 50	200 250	—
Output Admittance ( $I_C = 1.0 \text{ mA } V_{CE} = 5.0 \text{ V}$ ) ( $I_C = 5.0 \text{ mA } V_{CE} = 5.0 \text{ V}$ )	$h_{oe}$	—	75 125	$\mu\text{mhos}$ $\mu\text{mho}$
Collector Base Time Constant ( $I_C = 10 \text{ mA }, V_{CB} = 10 \text{ V}, f = 40 \text{ mHz}$ )	$r_b'C_c$	—	300	ps

(1) Pulse Test: PW  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 1.0\%$ .

MOTOROLA SMALL-SIGNAL TRANSISTORS, FETs AND DIODES